

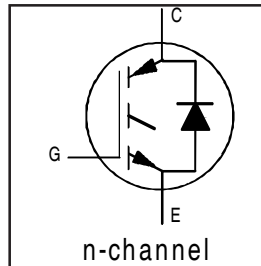
# IRG4PH50KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH  
ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated  
UltraFast IGBT

## Features

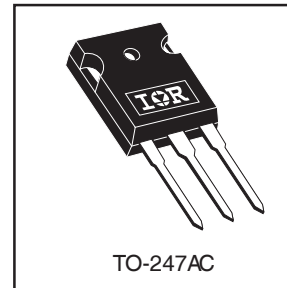
- High short circuit rating optimized for motor control,  $t_{sc} = 10\mu s$ ,  $V_{CC} = 720V$ ,  $T_J = 125^\circ C$ ,  $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- Tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes
- Lead-Free



$V_{CES} = 1200V$
$V_{CE(on) typ.} = 2.77V$
@ $V_{GE} = 15V, I_C = 24A$

## Benefits

- Latest generation 4 IGBT's offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- This part replaces the IRGPH50KD2 and IRGPH50MD2 products
- For hints see design tip 97003



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	45	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	24	
$I_{CM}$	Pulsed Collector Current ①	90	
$I_{LM}$	Clamped Inductive Load Current ②	90	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	16	
$I_{FM}$	Diode Maximum Forward Current	90	
$t_{sc}$	Short Circuit Withstand Time	10	$\mu s$
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	78	
$T_J$	Operating Junction and	-55 to +150	$^\circ C$
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

## Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	0.64	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	0.83	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
$Wt$	Weight	—	6 (0.21)	—	g (oz)

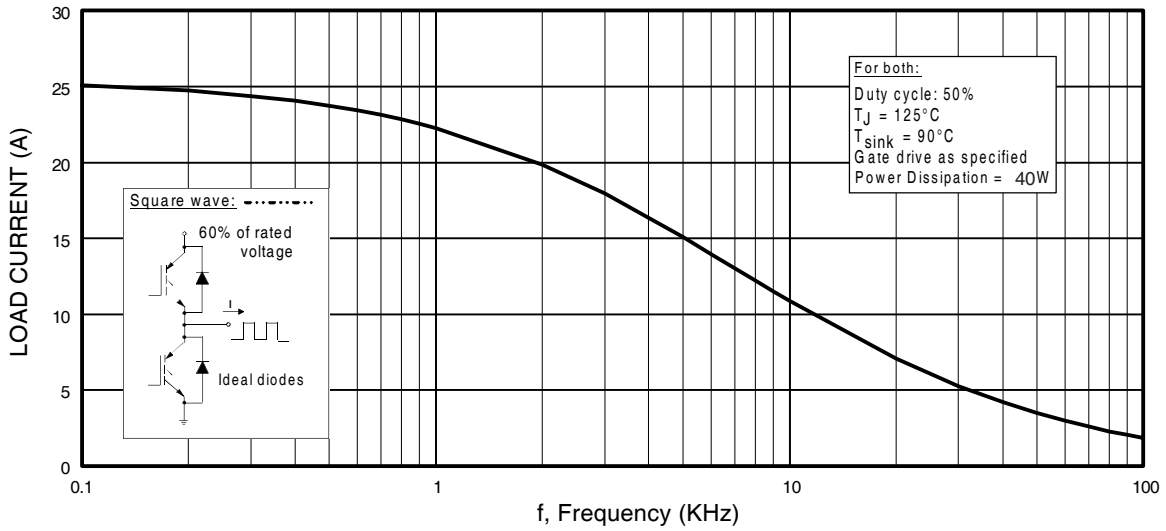
# IRG4PH50KDPbF

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

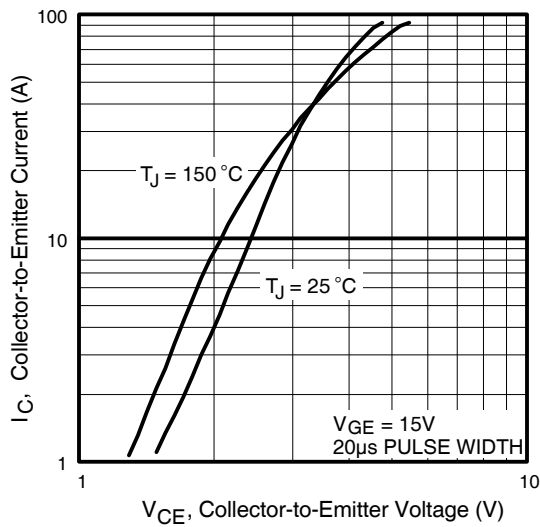
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage <sup>③</sup>	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.91	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.77	3.5	V	$I_C = 24A$ $I_C = 45A$ $I_C = 24A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig. 2, 5
		—	3.28	—		
		—	2.54	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance <sup>④</sup>	13	19	—	S	$V_{CE} = 100V, I_C = 24A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 1200V$
		—	—	6500		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
$V_{FM}$	Diode Forward Voltage Drop	—	2.5	3.5	V	$I_C = 16A$ $I_C = 16A, T_J = 150^\circ\text{C}$ See Fig. 13
		—	2.1	3.0		
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

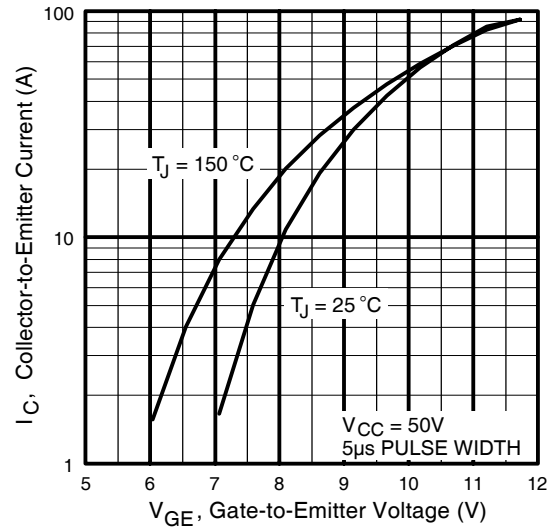
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	180	270	nC	$I_C = 24A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig.8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	25	38		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	70	110		
$t_{d(on)}$	Turn-On Delay Time	—	87	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 24A, V_{CC} = 800V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" and diode reverse recovery See Fig. 9,10,18
$t_r$	Rise Time	—	100	—		
$t_{d(off)}$	Turn-Off Delay Time	—	140	300		
$t_f$	Fall Time	—	200	300		
$E_{on}$	Turn-On Switching Loss	—	3.83	—	mJ	Measured 5mm from package
$E_{off}$	Turn-Off Switching Loss	—	1.90	—		
$E_{ts}$	Total Switching Loss	—	5.73	7.9	$\mu s$	$V_{CC} = 720V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 5.0\Omega$
$t_{sc}$	Short Circuit Withstand Time	10	—	—		
$t_{d(on)}$	Turn-On Delay Time	—	67	—	ns	$T_J = 150^\circ\text{C}$ , $I_C = 24A, V_{CC} = 800V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" and diode reverse recovery See Fig. 10,11,18
$t_r$	Rise Time	—	72	—		
$t_{d(off)}$	Turn-Off Delay Time	—	310	—		
$t_f$	Fall Time	—	390	—		
$E_{ts}$	Total Switching Loss	—	8.36	—	mJ	
$L_E$	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	2800	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
$C_{oes}$	Output Capacitance	—	140	—		
$C_{res}$	Reverse Transfer Capacitance	—	53	—		
$t_{rr}$	Diode Reverse Recovery Time	—	90	135	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$ 14
		—	164	245		
$I_{rr}$	Diode Peak Reverse Recovery Current	—	5.8	10	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$ 15
		—	8.3	15		
$Q_{rr}$	Diode Reverse Recovery Charge	—	260	675	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$ 16
		—	680	1838		
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During $t_b$	—	120	—	A/ $\mu s$	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$ 17
		—	76	—		



**Fig. 1 - Typical Load Current vs. Frequency**  
 (Load Current =  $I_{\text{RMS}}$  of fundamental)

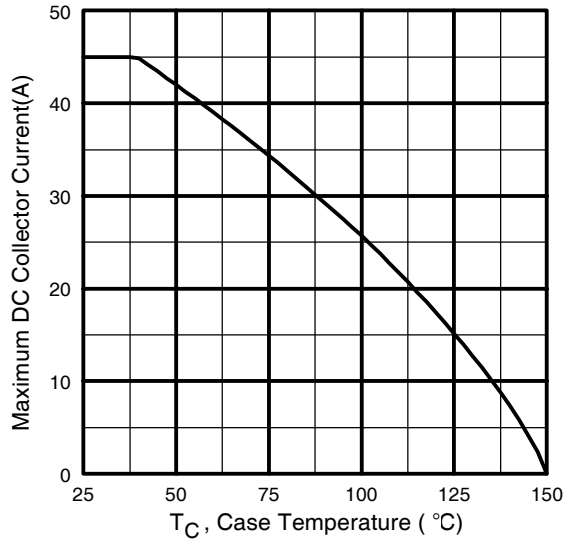


**Fig. 2 - Typical Output Characteristics**

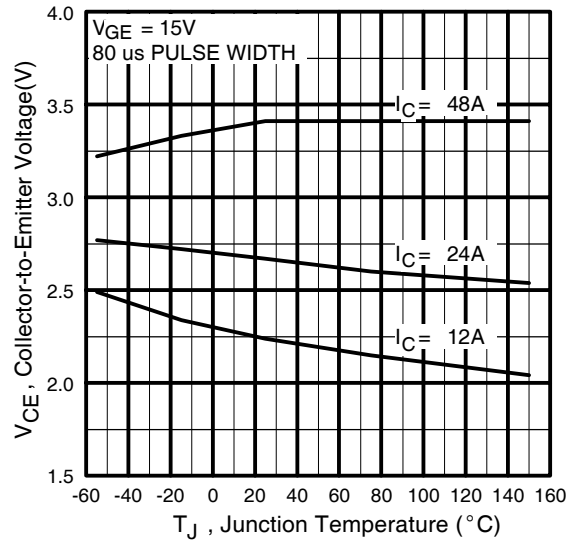


**Fig. 3 - Typical Transfer Characteristics**

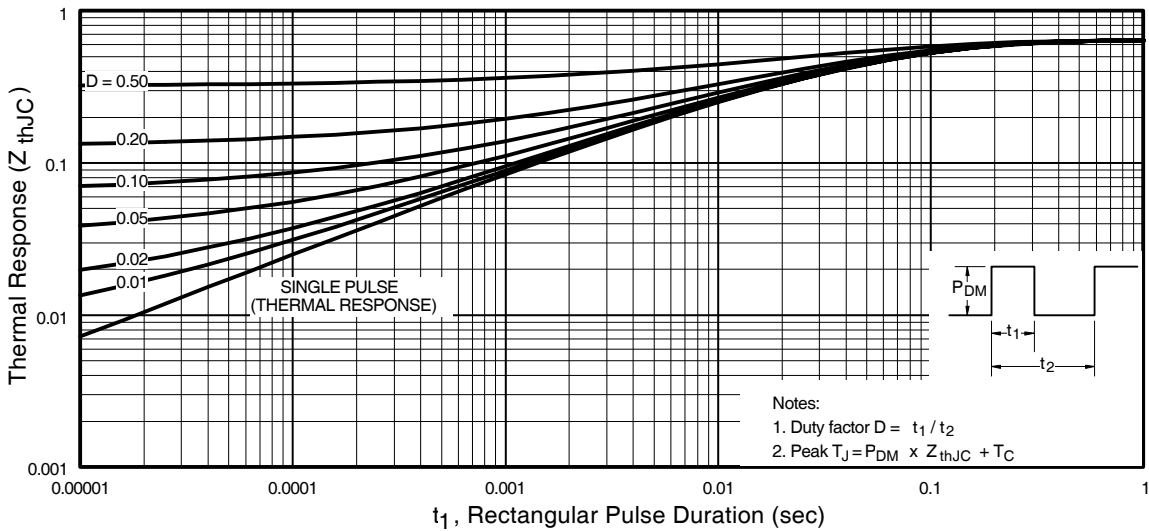
# IRG4PH50KDPbF



**Fig. 4** - Maximum Collector Current vs. Case Temperature

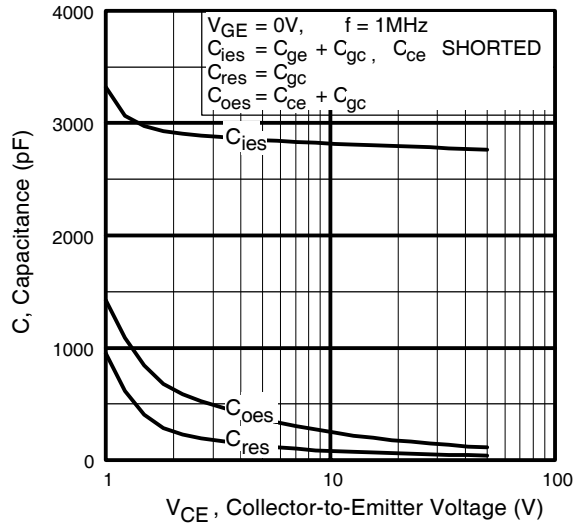


**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature

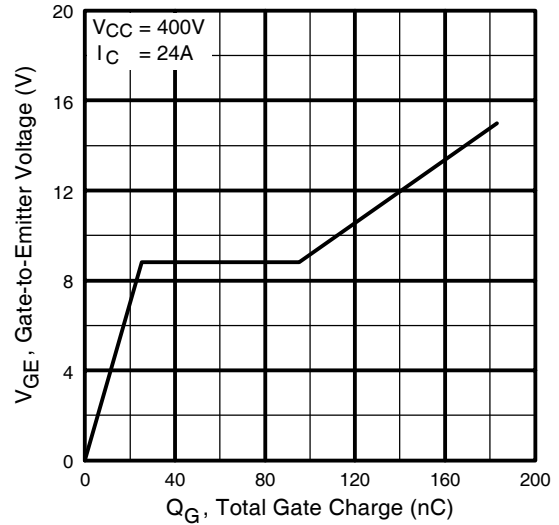


**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case

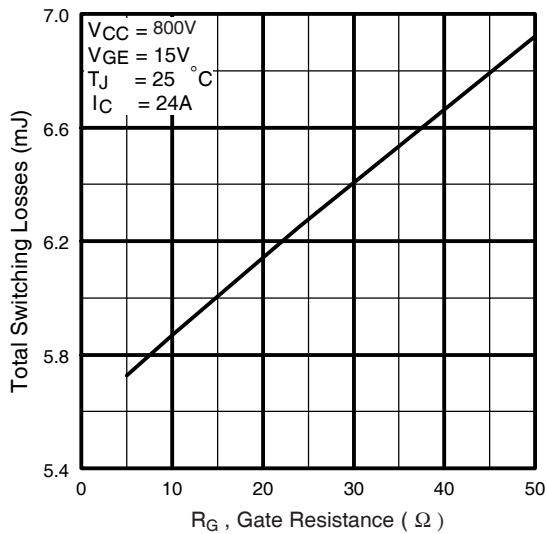
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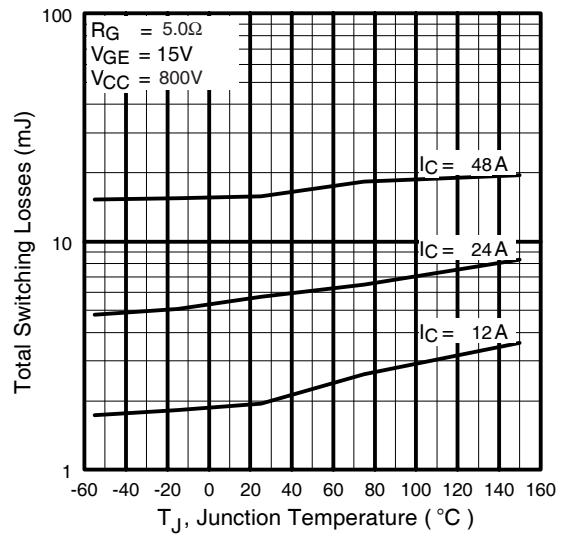
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



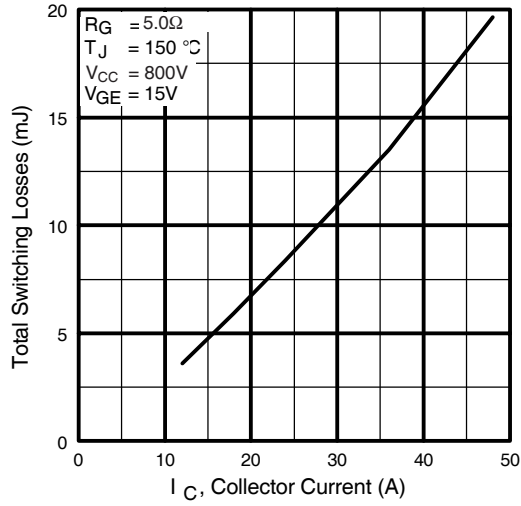
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



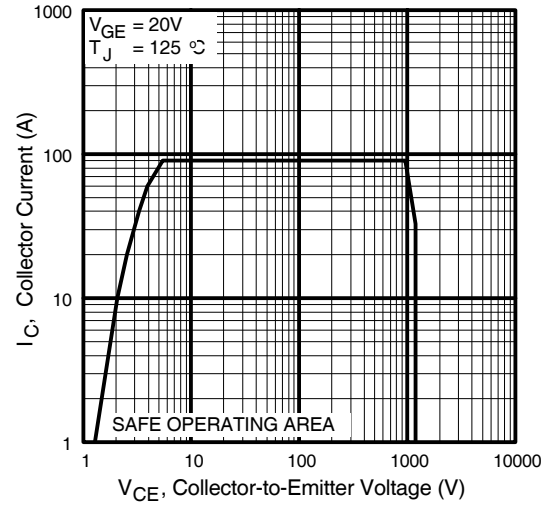
**Fig. 10** - Typical Switching Losses vs. Junction Temperature

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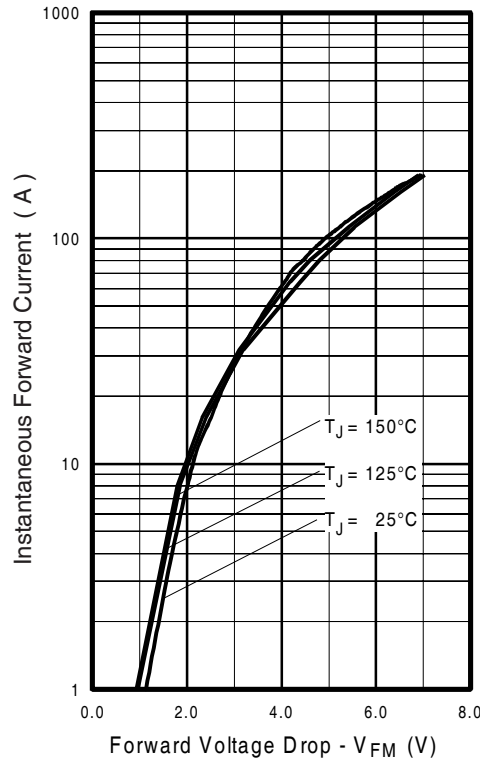
International  
**IR** Rectifier



**Fig. 11** - Typical Switching Losses vs. Collector Current



**Fig. 12** - Turn-Off SOA



**Fig. 13** - Typical Forward Voltage Drop vs. Instantaneous Forward Current

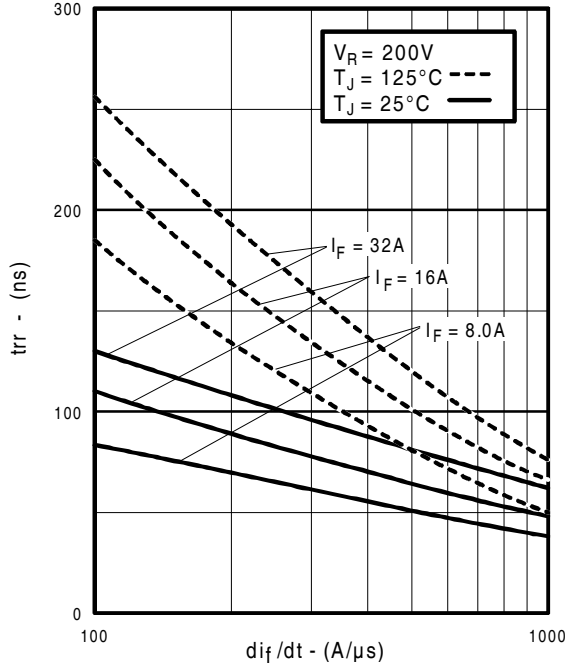


Fig. 14 - Typical Reverse Recovery vs.  $di/dt$

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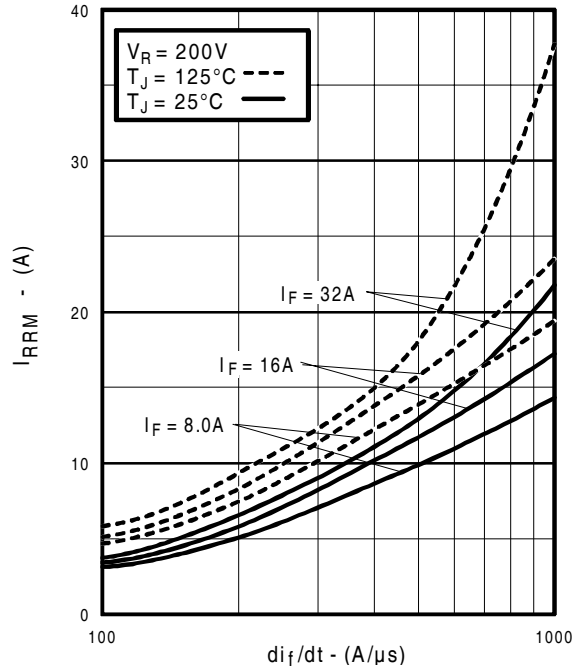


Fig. 15 - Typical Recovery Current vs.  $di/dt$

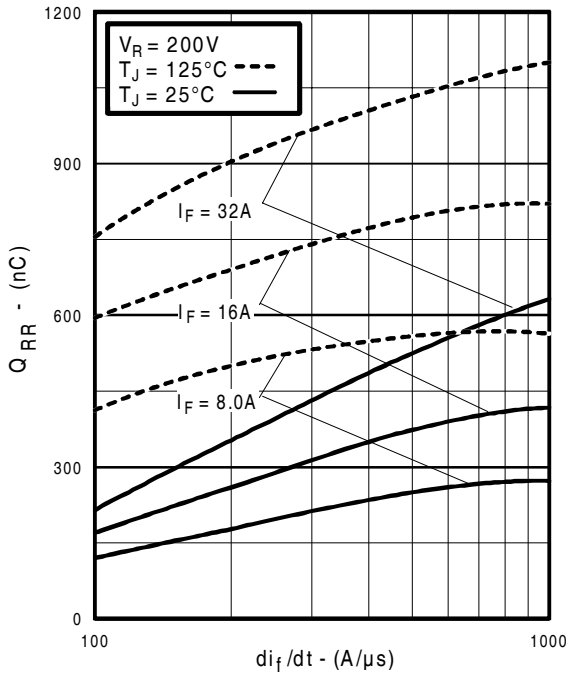


Fig. 16 - Typical Stored Charge vs.  $di/dt$

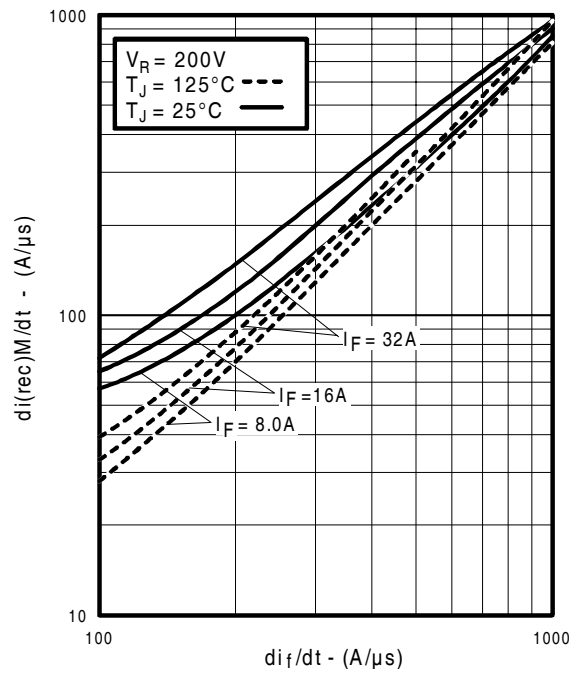
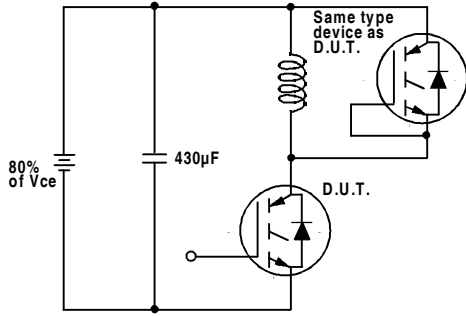
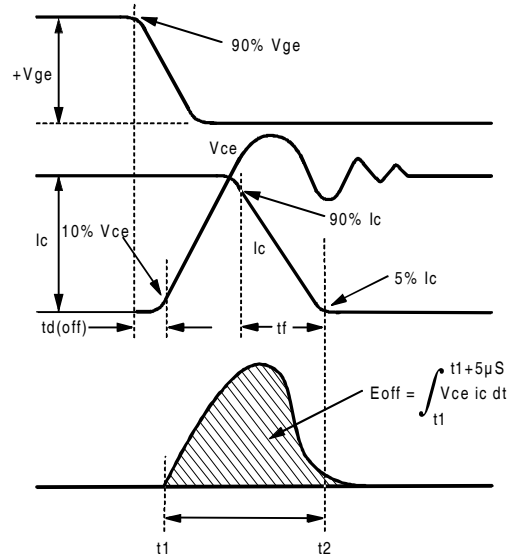


Fig. 17 - Typical  $di_{(rec)M}/dt$  vs.  $di/dt$

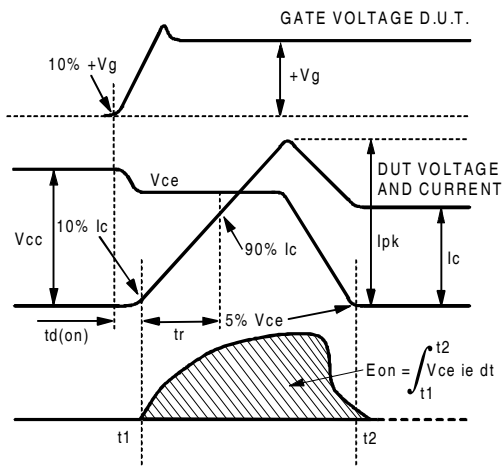
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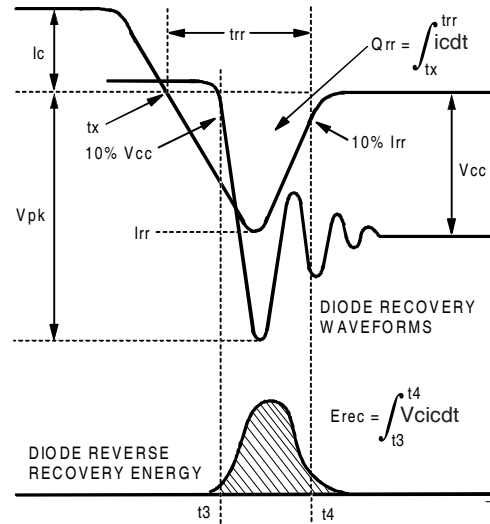
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$



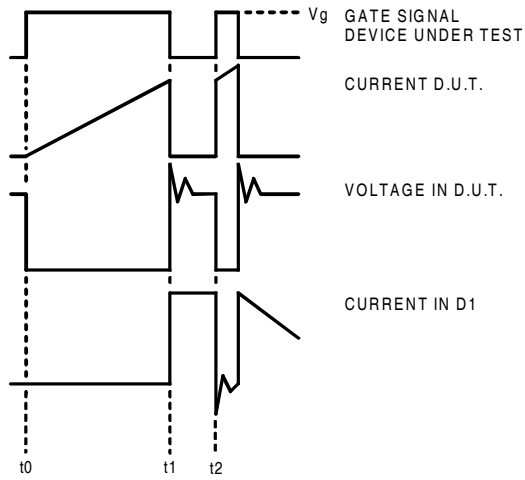


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

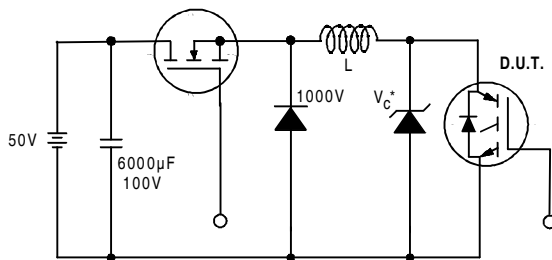


Figure 19. Clamped Inductive Load Test Circuit

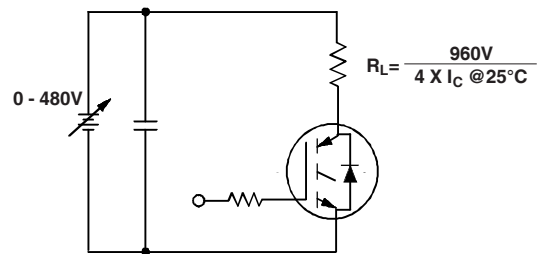


Figure 20. Pulsed Collector Current Test Circuit

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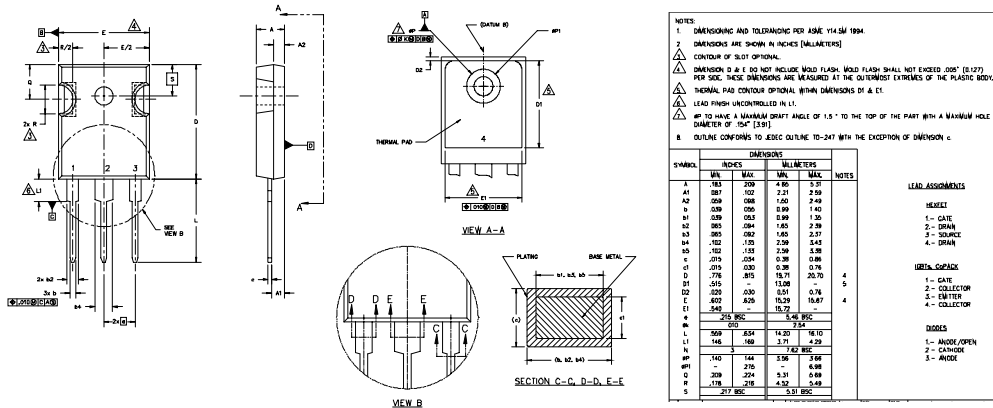


## Notes:

- ① Repetitive rating:  $V_{GE}=20V$ ; pulse width limited by maximum junction temperature (figure 20)
- ②  $V_{CC}=80\%(V_{CES})$ ,  $V_{GE}=20V$ ,  $L=10\mu H$ ,  $R_G=5.0\Omega$  (figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu s$ , single shot.

## TO-247AC Package Outline

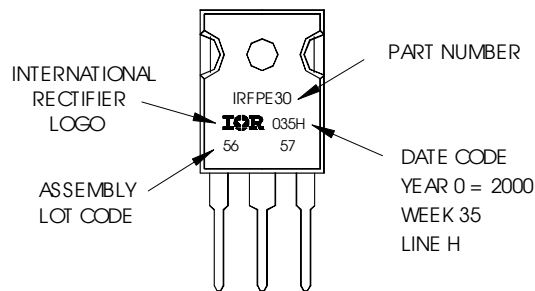
Dimensions are shown in millimeters (inches)



## TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30  
 WITH ASSEMBLY  
 LOT CODE 5657  
 ASSEMBLED ON WW 35, 2000  
 IN THE ASSEMBLY LINE "H"

**Note:** "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.



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 TAC Fax: (310) 252-7903  
 Visit us at [www.irf.com](http://www.irf.com) for sales contact information. 04/04

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>

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### Офис по работе с юридическими лицами:

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